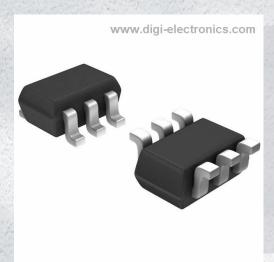


NTJD5121NT1G Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number NTJD5121NT1G-DG

Manufacturer onsemi

Manufacturer Product Number NTJD5121NT1G

Description MOSFET 2N-CH 60V 0.295A SC88

Detailed Description Mosfet Array 60V 295mA 250mW Surface Mount SC

-88/SC70-6/SOT-363



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
NTJD5121NT1G	onsemi
Series:	Product Status:
	Active
Technology:	Configuration:
MOSFET (Metal Oxide)	2 N-Channel (Dual)
FET Feature:	Drain to Source Voltage (Vdss):
Logic Level Gate	60V
Current - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ Id, Vgs:
295mA	1.60hm @ 500mA, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2.5V @ 250µA	0.9nC @ 4.5V
Input Capacitance (Ciss) (Max) @ Vds:	Power - Max:
26pF @ 20V	250mW
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
6-TSSOP, SC-88, SOT-363	SC-88/SC70-6/SOT-363
Base Product Number:	
NTJD5121	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

8541.21.0095

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MOSFET - Power, Dual, N-Channel With ESD Protection, SC-88 60 V, 295 mA NTJD5121N, NVJD5121N

Features

- Low R_{DS(on)}
- Low Gate Threshold
- Low Input Capacitance
- ESD Protected Gate
- NVJD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

Applications

- Low Side Load Switch
- DC-DC Converters (Buck and Boost Circuits)

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parame	Symbol	Value	Unit		
Drain-to-Source Voltage	V _{DSS}	60	V		
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain	Steady	T _A = 25°C	I _D	295	mA
Current (Note 1)	State	T _A = 85°C		212	
	t ≤ 5 s	T _A = 25°C		304	
		T _A = 85°C		219	
Power Dissipation (Note 1)	Steady T _A = 25°C		P _D	250	mW
	t ≤ 5 s			266	
Pulsed Drain Current	t _p =	= 10 μs	I _{DM}	900	mA
Operating Junction and S	T _J , T _{STG}	–55 to 150	°C		
Source Current (Body Did	ode)		I _S	210	mA
Lead Temperature for Sol (1/8" from case for 10 s)	TL	260	°C		
Gate-Source ESD Rating	ESD _{HBM}	2000	V		
Gate-Source ESD Rating	g (MM)	-	ESD _{MM}	200	V

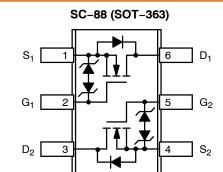
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State	$R_{\theta JA}$	467	°C/W
Junction-to-Ambient - t ≤ 5 s	$R_{\theta JA}$	412	
Junction-to-Lead - Steady State	$R_{\theta JL}$	252	

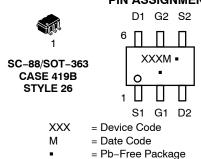
1

V _{(BR)DSS}	R _{DS(on)} MAX	I _D Max
60 V	1.6 Ω @ 10 V	295 mA
00 V	2.5 Ω @ 4.5 V	293 IIIA



Top View

MARKING DIAGRAM & PIN ASSIGNMENT



(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information ion page 5 of this data sheet.

Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

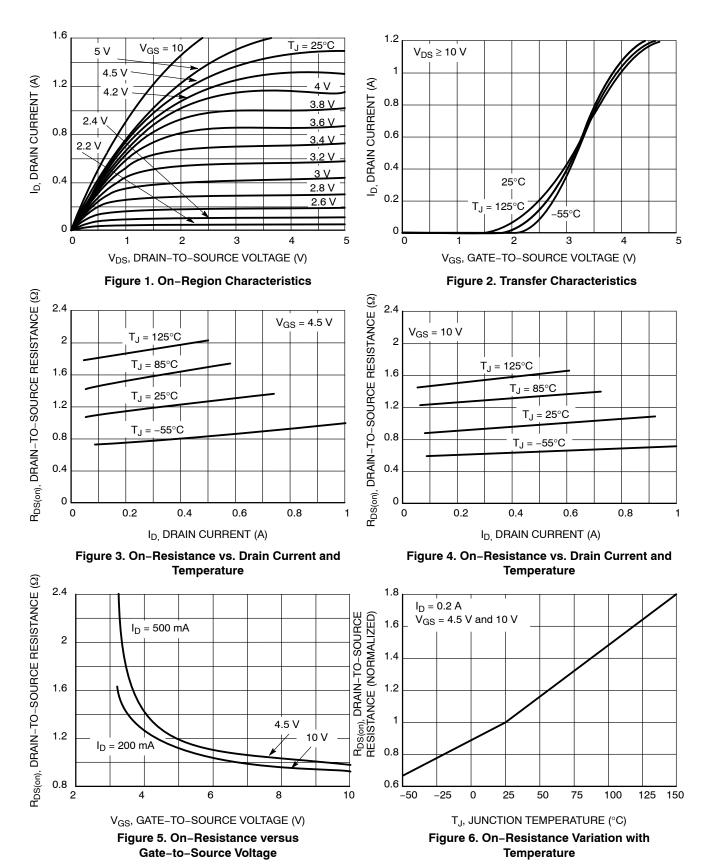
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Con	dition	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		•		
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D	= 250 μΑ	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I _D = 250 μA, r	ef to 25°C		92		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$,	T _J = 25°C			1.0	μА
		$V_{DS} = 60 \text{ V}$	T _J = 125°C			500	7
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 V, V_{G}$	_{iS} = ±20 V			±10	μА
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D	= 250 μΑ	1.0	1.7	2.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J				4.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$ $V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$			1.0	1.6	Ω
					1.2	2.5	7
Forward Transconductance	9FS	V _{DS} = 5 V, I _D = 200 mA			80		S
Gate Resistance	R_{G}				536		Ω
CHARGES AND CAPACITANCES					•		
Input Capacitance	C _{ISS}				26		pF
Output Capacitance	C _{OSS}	$V_{GS} = 0 \text{ V, f} = V_{DS} = 2$	1.0 MHz,		4.4		1
Reverse Transfer Capacitance	C _{RSS}	- 503			2.5		7
Total Gate Charge	Q _{G(TOT)}				0.9		nC
Threshold Gate Charge	Q _{G(TH)}	V _{GS} = 4.5 V, V	ns = 25 V,		0.2		7
Gate-to-Source Charge	Q_{GS}	I _D = 200	mA		0.3		7
Gate-to-Drain Charge	Q_{GD}				0.28		7
SWITCHING CHARACTERISTICS (No	ote 3)		-				
Turn-On Delay Time	t _{d(on)}				22		ns
Rise Time	t _r	V _{GS} = 4.5 V, V	nn = 25 V.		34		7
Turn-Off Delay Time	t _{d(off)}	$I_D = 200 \text{ mA}, R_G = 25 \Omega$			34		7
Fall Time	t _f				32		7
DRAIN-SOURCE DIODE CHARACTE	RISTICS		•		-	-	
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V,	T _J = 25°C		0.8	1.2	٧
		$I_{S} = 200 \text{ mA}$ $T_{J} = 85^{\circ}$			0.7		1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
2. Pulse Test: pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$.
3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

(T_J = 25°C UNLESS OTHERWISE NOTED)



TYPICAL PERFORMANCE CURVES

(T_J = 25°C UNLESS OTHERWISE NOTED)

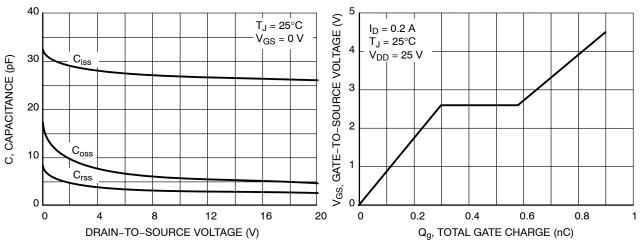


Figure 7. Capacitance Variation

Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

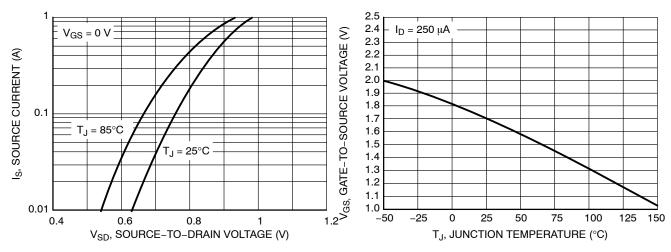


Figure 9. Diode Forward Voltage vs. Current

Figure 10. Threshold Voltage with Temperature

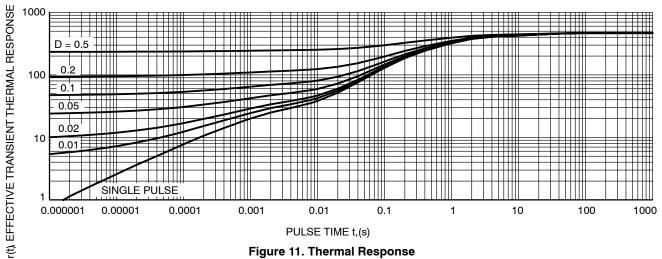


Figure 11. Thermal Response

Table 1. ORDERING INFORMATION

Part Number	Marking	Package	Shipping [†]
NTJD5121NT1G	TF	SC-88 (Pb-Free)	3000 / Tape & Reel
NTJD5121NT2G	TF	SC-88 (Pb-Free)	3000 / Tape & Reel
NVJD5121NT1G*	VTF	SC-88 (Pb-Free)	3000 / Tape & Reel
NVJD5121NT1G-M06*	VTF	SC-88 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NVJD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



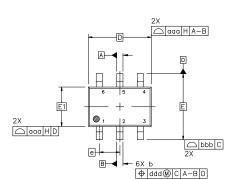
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

DATE 18 APR 2024

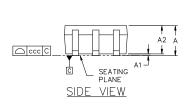


NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
- DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 DATUMS A AND B ARE DETERMINED AT DATUM H.
- DIMENSIONS 6 AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

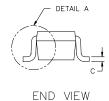
DIM

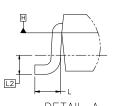
MIN



6X 0.30 -

TOP VIEW





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			AIL	<u>A</u>
	2	UΑ	LE 2:	1

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code = Date Code*

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED MOUNTING FOOTPRINT*

6X 0.66

2.50

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLES ON PAGE 2

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A1	0.00		0.10		
A2	0.70	0.90	1.00		
b	0.15	0.20	0.25		
С	0.08	0.15	0.22		
D	:	2.00 BSC	;		
E		2.10 BSC	:		
E1	1.25 BSC				
е		0.65 BSC	,		
L	0.26 0.36 0.46				
L2	0.15 BSC				
aaa	0.15				
bbb	0.30				
ccc	0.10				
ddd		0.10			

MILLIMETERS

NOM

MAX.

1.10

SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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